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Application No.	Applicant(s)	
Examiner	OKITA, YOICHI Art Unit	
Hoai v. Pham	2814	
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.		
1. This communication is responsive to <u>01/19/2004</u> .		
2. The allowed claim(s) is/are <u>13-23</u> .		
3. The drawings filed on 19 January 2004 are accepted by the Examiner.		
 4.		
6. ☐ Interview Summary Paper No./Mail Dat 8), 7. ☐ Examiner's Amendr		
	Ars on the cover sheet with the country of the cover sheet with the country of this application is subject to and MPEP 1308. Examiner. der 35 U.S.C. § 119(a)-(d) or (f). been received. been received in Application No. Oscillation of this communication to file a reply entry of this application. Itted. Note the attached EXAMINER's reason(s) why the oath or declarate to be submitted. on's Patent Drawing Review (PTO-standard of the Amendment / Comment or in the Country of the Cou	

PRIMARY EXAMINER

Application/Control Number: 10/765,898 Page 2

Art Unit: 2814

DETAILED ACTION

Allowable Subject Matter

- 1. Claims 13-23 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: the prior of record fails to disclose the combination of the process steps of forming a semiconductor device recited in the base claim 13, including the combination of the process steps comprising: forming a second resist pattern, that have a width equal to or smaller than a pattern width of the upper electrode of the capacitor, on the upper electrode of the capacitor, and etching at least one of the dielectric film and the first conductive film by using the second resist pattern as a mask, while exposing a part of an upper surface of the upper electrode of the capacitor by retreating side portion of the second resist pattern.
- 3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hoai v. Pham whose telephone number is 571-272-1715. The examiner can normally be reached on M-F.
- 4. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M. Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 10/765,898

Art Unit: 2814

5. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

HOAI PHAM
PRIMARY EXAMINER

Page 3